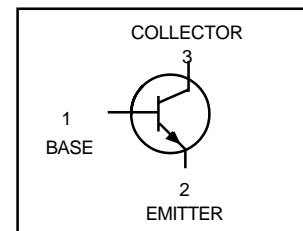
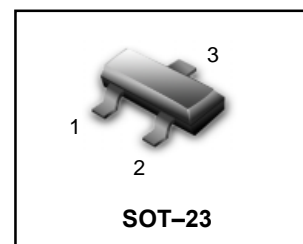


General Purpose Transistors NPN Silicon

FEATURE

- High current capacity in compact package.
I_C = 1.8 A.
- Epitaxial planar type.
- Pb-Free Package is available.

MARKING: 618


MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	25	V
Collector-Base Voltage	V _{CBO}	40	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	1800	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,(1) T _A =25°C	P _D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance,Junction to Ambient	R _{θJA}	556	°C/W
Total Device Dissipation Alumina Substrate,(2) T _A =25°C	P _D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance,Junction to Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

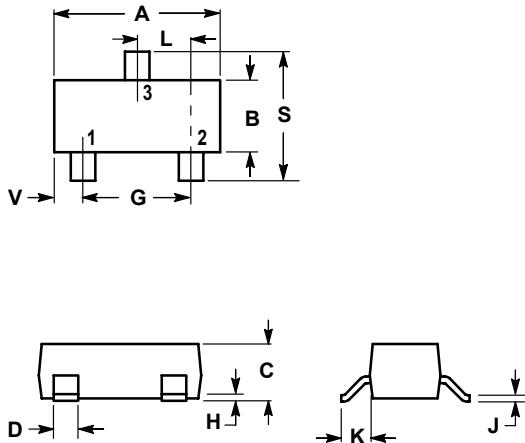
Collector-Emitter Breakdown Voltage (I _C =1.0mA)	V _{(BR)CEO}	25	-	-	V
Emitter-Base Breakdown Voltage (I _E =100μA)	V _{(BR)EBO}	5	-	-	V
Collector-Base Breakdown Voltage (I _C =100μA)	V _{(BR)CBO}	40	-	-	V
Collector Cutoff Current (V _{CB} =35V)	I _{CBO}	-	-	150	nA
Emitter Cutoff Current (V _{EB} =4V)	I _{EBO}	-	-	150	nA

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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ON CHARACTERISTICS

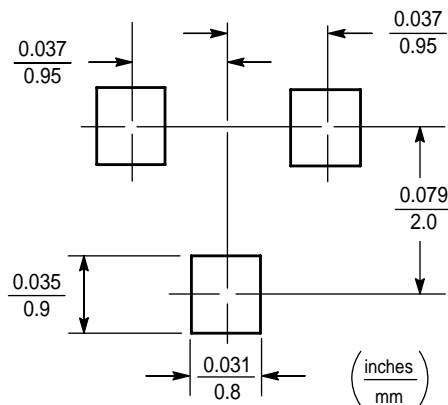
DC Current Gain I _C =100mA, V _{CE} =1V	h _{FE}	100	-	600	
Collector-Emitter Saturation Voltage (I _C =800mA I _B =80mA)	V _{CE(S)}	-	-	0.5	V

SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. BASE
2. EMITTER
3. COLLECTOR



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